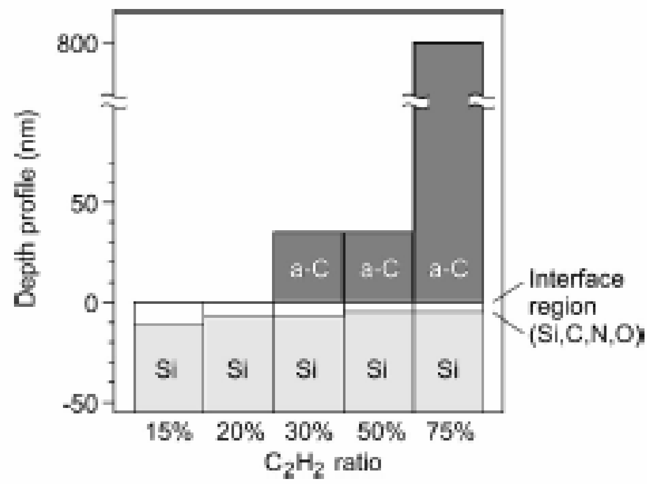

FIG. 3. Summary of depth-resolved Auger chemical analysis on the unpatterned Si areas of samples deposited at different C_2H_2 ratios. Below 30%, no a-C is detected. In all PECVD cases, a thin interface layer is detected due to the reaction of ionized C_2H_2 /NH_3 species in the plasma with the Si surface.

圖 2.1 乙炔氨氣反應後表面成分 Auger 分析[Teo-2001-79]

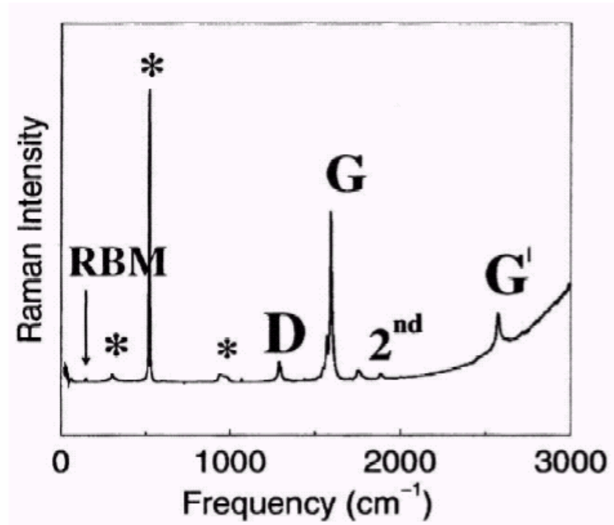

圖 2. 2 單壁碳奈米管拉曼頻譜示意圖[Dresselhaus-2002-2043]

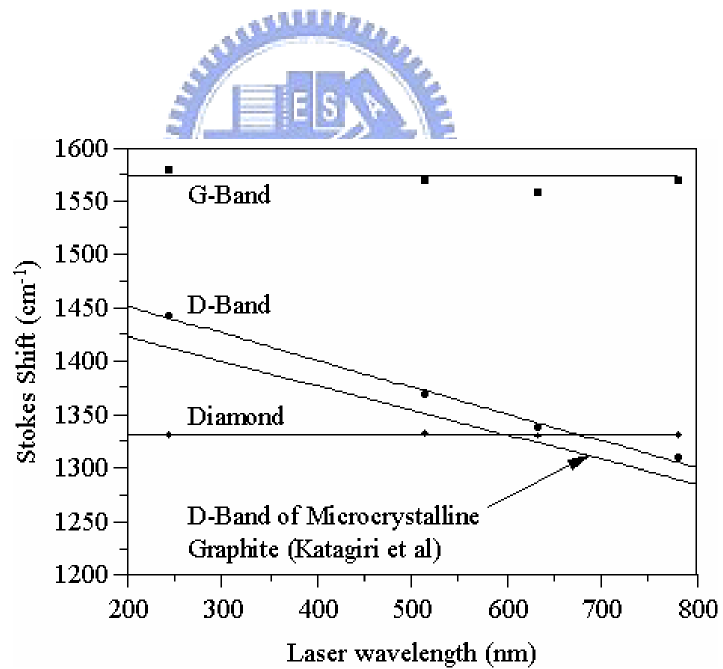

圖 2.3 雷射光源波長與表現之強度位移區

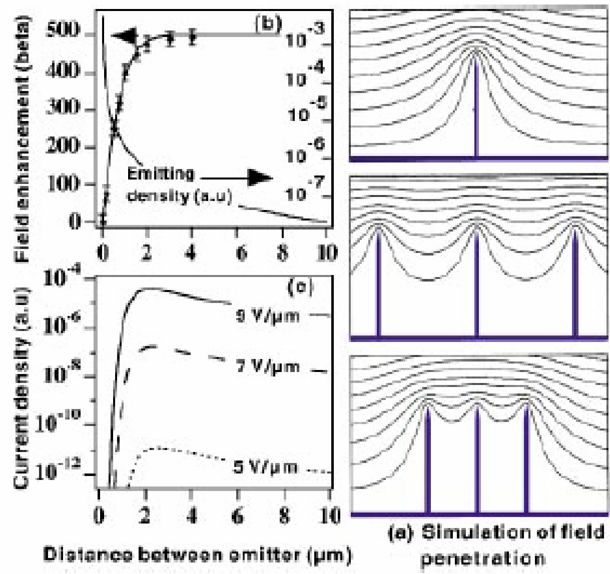

圖 2.4 影響場效發射示意圖[Nilsson-2000-2071]

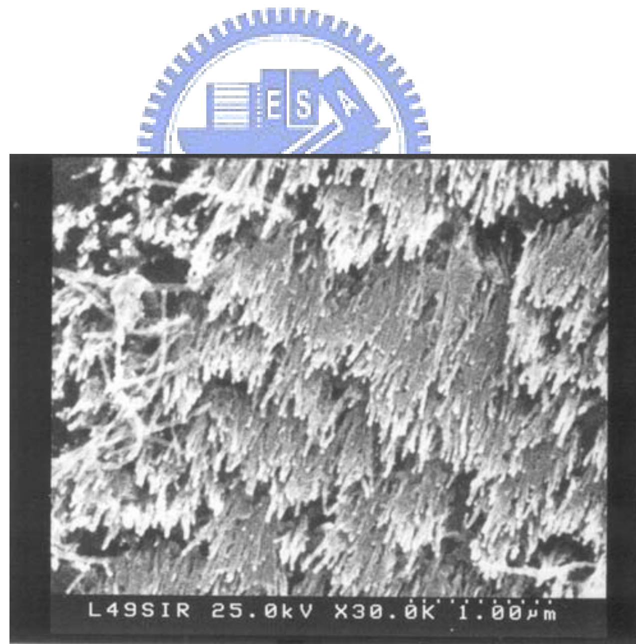

圖 2.5 場發射效果不佳可能之外觀